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ABSTRACT

The objective of the invention is to provide a method that can form connection holes reliably by making contact resistance low and uniform, and to provide semiconductor devices produced with this. Insulating layer 3, that includes SOG layer 7, is plasma etched using an etching gas with a small quantity of a gas with a low C/F ratio, such as CHF₃, mixed with a gas with a high C/F ratio, such as C₄F₈/Ar/O₂ at a ratio of 1:3.